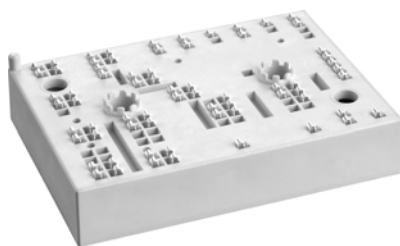


SKiiP 38NAB12T4V1



MiniSKiiP® 3

Converter-Inverter-Brake
(CIB)

SKiiP 38NAB12T4V1

Features*

- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

Typical Applications

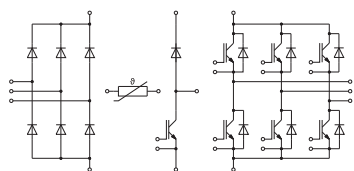
- Inverter up to 41 kVA
- Typical motor power 22 kW

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_J \leq 150^\circ\text{C}$ (recommended $T_{J,op} = -40 \dots +150^\circ\text{C}$)
- For short circuit: Soft R_{Goff} recommended
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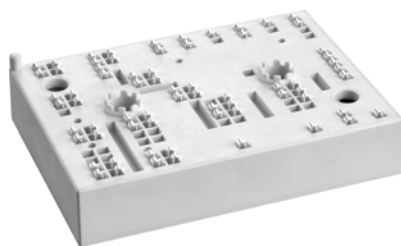
Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Inverter - IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	115	A
	T _j = 175 °C	T _s = 70 °C	93	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	140	A
	T _j = 175 °C	T _s = 70 °C	114	A
I _{Cnom}			100	A
I _{CRM}			300	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	μs
T _j			-40 ... 175	°C
Chopper - IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	115	A
	T _j = 175 °C	T _s = 70 °C	93	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	140	A
	T _j = 175 °C	T _s = 70 °C	114	A
I _{Cnom}			100	A
I _{CRM}			300	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	μs
T _j			-40 ... 175	°C
Inverse - Diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	99	A
	T _j = 175 °C	T _s = 70 °C	79	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	116	A
	T _j = 175 °C	T _s = 70 °C	93	A
I _{FRM}			300	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 150 °C		550	A
T _j			-40 ... 175	°C
Freewheeling - Diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	100	A
	T _j = 175 °C	T _s = 70 °C	79	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	116	A
	T _j = 175 °C	T _s = 70 °C	93	A
I _{FRM}			300	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 150 °C		550	A
T _j			-40 ... 175	°C



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- UL recognized: File no. E63532

Typical Applications

- Inverter up to 41 kVA
- Typical motor power 22 kW

Remarks

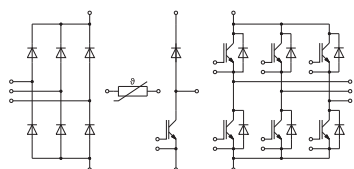
- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- For short circuit: Soft R_{Goff} recommended
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Rectifier - Diode				
V _{RRM}	T _j = 25 °C		1600	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	117	A
	T _j = 150 °C	T _s = 70 °C	86	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	136	A
	T _j = 150 °C	T _s = 70 °C	101	A
I _{FSM}	t _p = 10 ms	T _j = 25 °C	1000	A
	sin 180°	T _j = 150 °C	890	A
i ² t	t _p = 10 ms	T _j = 25 °C	5000	A ² s
	sin 180°	T _j = 150 °C	3960	A ² s
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C, 20 A per spring		80	A
T _{stg}	module without TIM		-40 ... 125	°C
V _{isol}	AC sinus 50 Hz, 1 min		2500	V

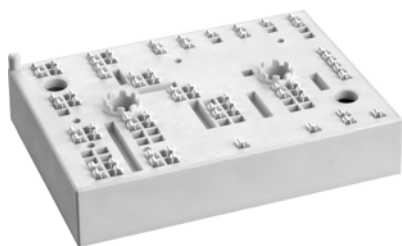
Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 100 \text{ A}$ $V_{GE} = 15 \text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	1.80	2.05	V
		$T_j = 150^\circ\text{C}$	2.20	2.40	V
V_{CE0}	chiplevel	$T_j = 25^\circ\text{C}$	0.80	0.90	V
		$T_j = 150^\circ\text{C}$	0.70	0.80	V
r_{CE}	$V_{GE} = 15 \text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	10	12	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	15	16	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 4 \text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0 \text{ V}$, $V_{CE} = 1200 \text{ V}$, $T_j = 25^\circ\text{C}$			1	mA
C_{ies}	$V_{CE} = 25 \text{ V}$ $V_{GE} = 0 \text{ V}$	$f = 1 \text{ MHz}$	6.15		nF
C_{oes}		$f = 1 \text{ MHz}$	0.41		nF
C_{res}		$f = 1 \text{ MHz}$	0.35		nF
Q_G	$V_{GE} = -8 \text{ V} \dots +15 \text{ V}$		565		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		7.5		Ω
$t_{d(on)}$	$V_{CC} = 600 \text{ V}$ $I_C = 100 \text{ A}$	$T_j = 150^\circ\text{C}$	160		ns
t_r	$R_{G on} = 1 \Omega$	$T_j = 150^\circ\text{C}$	35		ns
E_{on}	$R_{G off} = 1 \Omega$	$T_j = 150^\circ\text{C}$	11.2		mJ
$t_{d(off)}$		$T_j = 150^\circ\text{C}$	390		ns
t_f		$T_j = 150^\circ\text{C}$	75		ns
E_{off}	$V_{GE} = +15/-15 \text{ V}$	$T_j = 150^\circ\text{C}$	10		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8 \text{ W/(mK)}$		0.48		K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5 \text{ W/(mK)}$		0.34		K/W



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SKiiP 38NAB12T4V1



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Features*

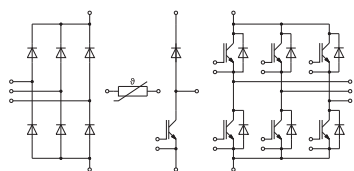
- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

Typical Applications

- Inverter up to 41 kVA
- Typical motor power 22 kW

Remarks

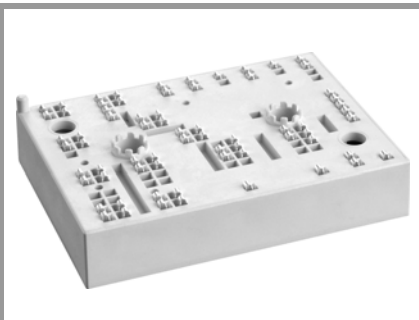
- Max. case temperature limited to $T_C=125^\circ\text{C}$
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- For short circuit: Soft R_{Goff} recommended
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Chopper - IGBT						
V _{CE(sat)}	I _C = 100 A	T _j = 25 °C		1.80	2.05	V
	V _{GE} = 15 V chiplevel	T _j = 150 °C		2.20	2.40	V
V _{CE0}	chiplevel	T _j = 25 °C		0.80	0.90	V
		T _j = 150 °C		0.70	0.80	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		10	12	mΩ
	chiplevel	T _j = 150 °C		15	16	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 4 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 1200 V, T _j = 25 °C				1	mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		6.15		nF
C _{oes}		f = 1 MHz		0.41		nF
C _{res}		f = 1 MHz		0.35		nF
Q _G	V _{GE} = - 8 V...+ 15 V			565		nC
R _{Gint}	T _j = 25 °C			7.5		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		160		ns
t _r	I _C = 100 A	T _j = 150 °C		35		ns
E _{on}	R _{G on} = 1 Ω	T _j = 150 °C		11.2		mJ
t _{d(off)}	R _{G off} = 1 Ω	T _j = 150 °C		390		ns
t _f		T _j = 150 °C		75		ns
E _{off}		V _{GE} = +15/-15 V	T _j = 150 °C		10	
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(mK)			0.48		K/W
R _{th(j-s)}	per IGBT, λ _{paste} =2.5 W/(mK)			0.34		K/W
Inverse - Diode						
V _F = V _{EC}	I _F = 100 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.15	2.47	V
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
		T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		9.0	10	mΩ
		T _j = 150 °C		13	14	mΩ
I _{RRM}	I _F = 100 A	T _j = 150 °C		82		A
Q _{rr}	di/dt _{off} = 2400 A/μs	T _j = 150 °C		16.4		μC
E _{rr}	V _{GE} = -15 V V _{CC} = 600 V	T _j = 150 °C		6.5		mJ
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			0.66		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			0.52		K/W
Freewheeling - Diode						
V _F = V _{EC}	I _F = 100 A	T _j = 25 °C		2.20	2.52	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.15	2.47	V
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
		T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		9.0	10	mΩ
		T _j = 150 °C		13	14	mΩ
I _{RRM}	I _F = 100 A	T _j = 150 °C		82		A
Q _{rr}	di/dt _{off} = 2400 A/μs	T _j = 150 °C		16.4		μC
E _{rr}	V _{GE} = -15 V V _{CC} = 600 V	T _j = 150 °C		6.5		mJ
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			0.66		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			0.52		K/W

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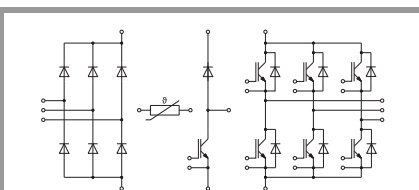
Typical Applications

- Inverter up to 41 kVA
- Typical motor power 22 kW

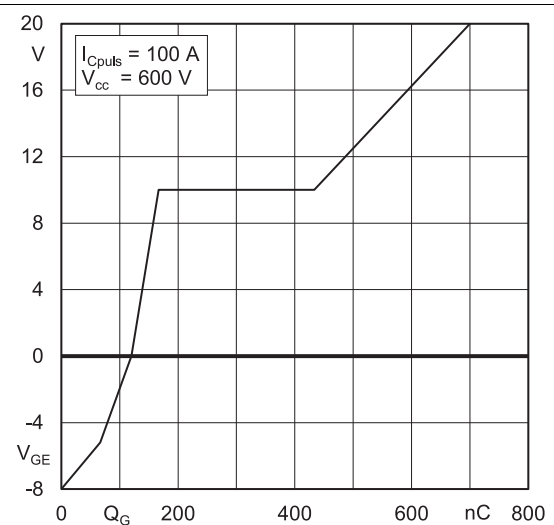
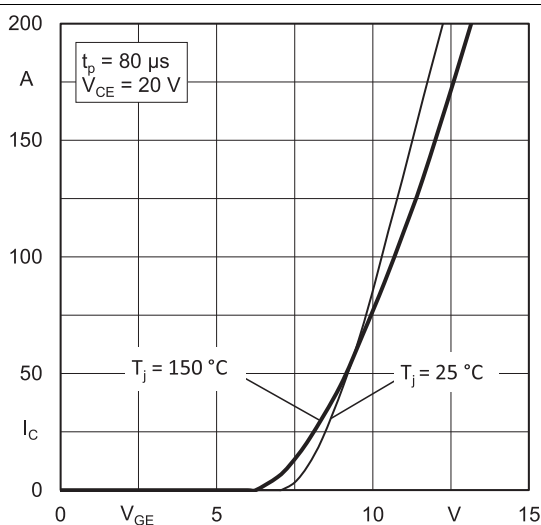
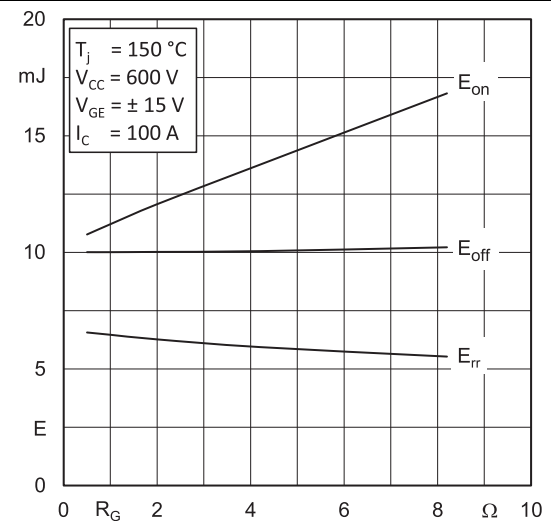
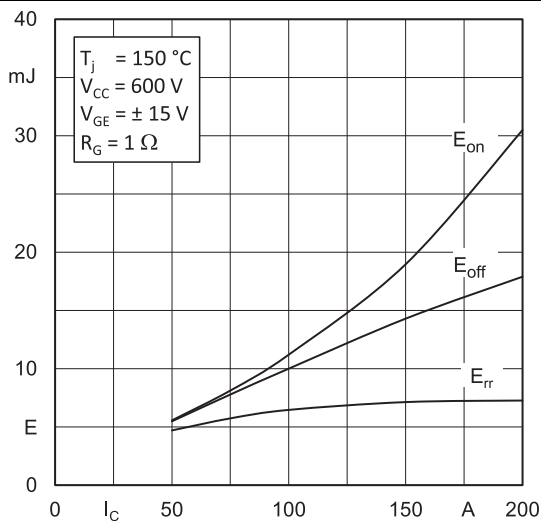
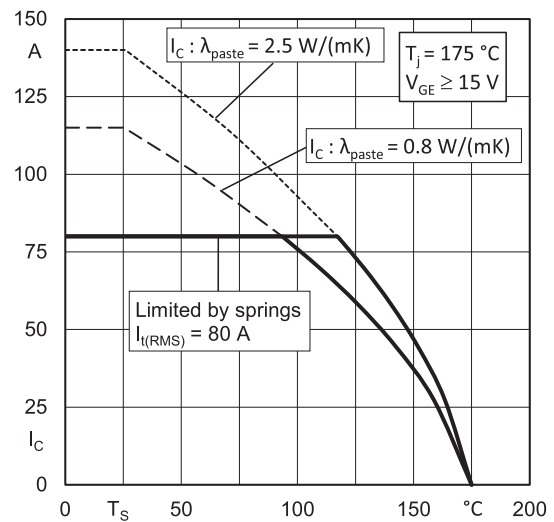
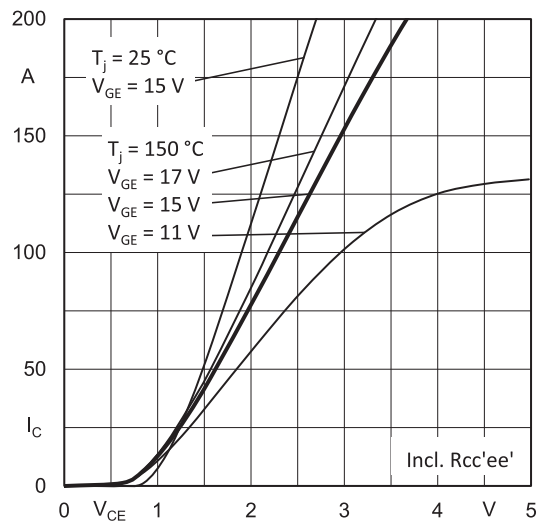
Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- For short circuit: Soft R_{Goff} recommended
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Rectifier - Diode						
V _F = V _{EC}	I _F = 45 A	T _j = 25 °C		1.00	1.21	V
	chiplevel	T _j = 125 °C		0.90	1.10	V
V _{F0}	chiplevel	T _j = 25 °C		0.88	0.98	V
		T _j = 125 °C		0.73	0.83	V
r _F	chiplevel	T _j = 25 °C		2.7	5.1	mΩ
		T _j = 125 °C		3.8	6.0	mΩ
I _R	T _j = 145 °C, V _{RRM}				1.1	mA
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			0.7		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			0.56		K/W
Module						
M _s	to heat sink		2		2.5	Nm
w				82		g
L _{CE}				-		nH
Temperature Sensor						
R ₁₀₀	T _r =100°C (R ₂₅ =1000Ω)			1670 ± 3%		Ω
R _(T)	R _(T) =1000Ω[1+A(T-25°C)+B(T-25°C) ²] , A = 7.635*10 ⁻³ °C ⁻¹ , B = 1.731*10 ⁻⁵ °C ⁻²					



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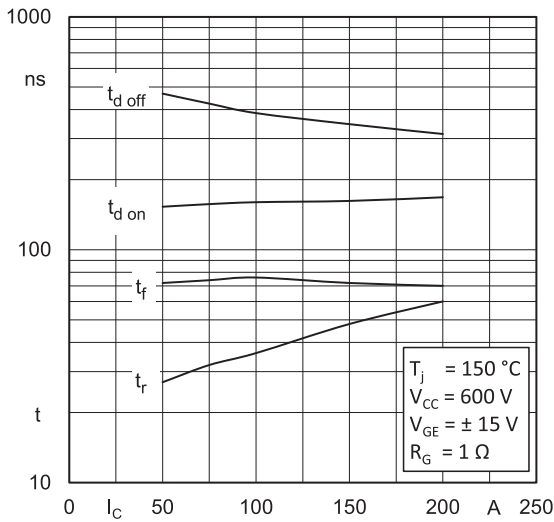


Fig. 7: Typ. switching times vs. I_C

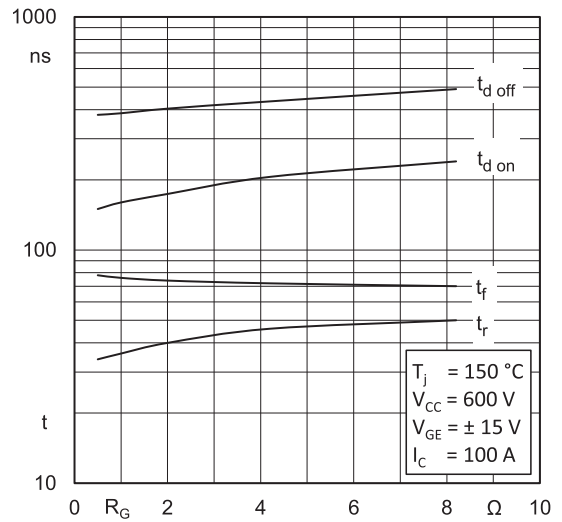


Fig. 8: Typ. switching times vs. gate resistor R_G

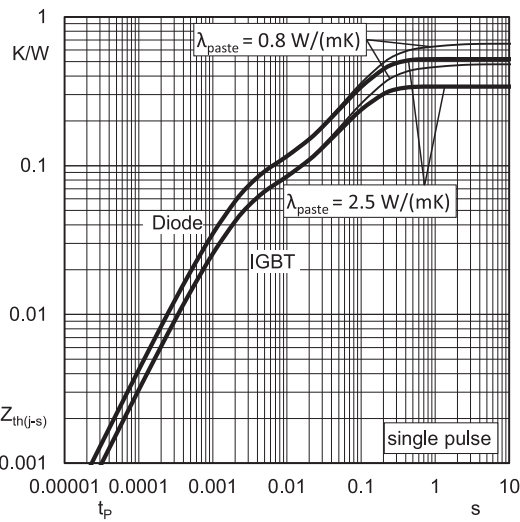


Fig. 9: Typ. transient thermal impedance

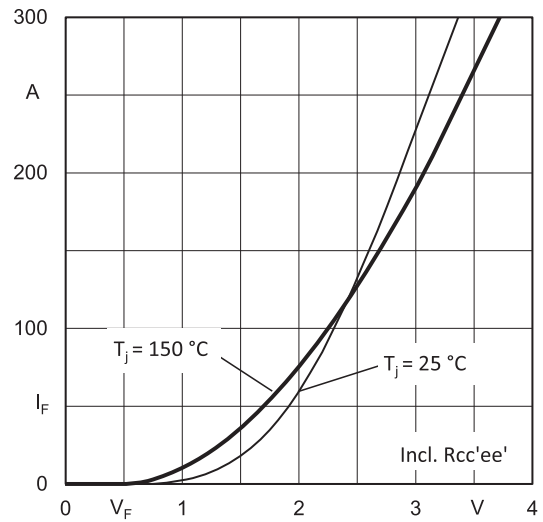


Fig. 10: Typ. CAL diode forward characteristic

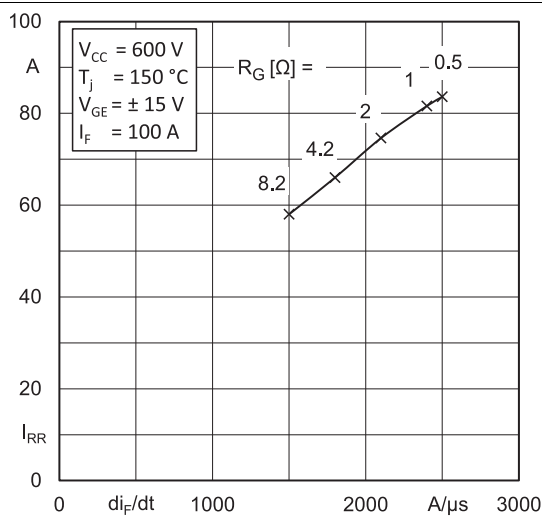


Fig. 11: Typ. CAL diode peak reverse recovery current

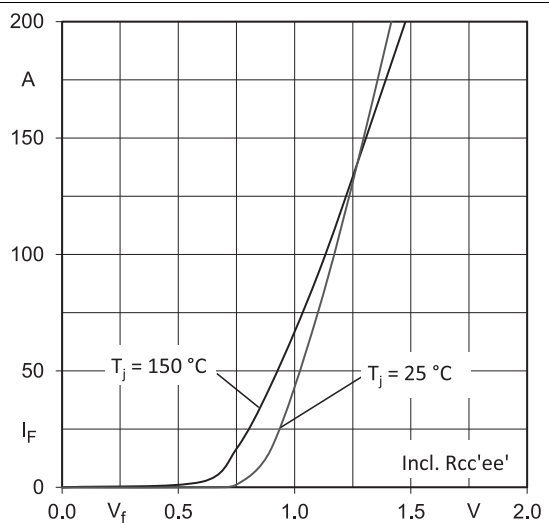
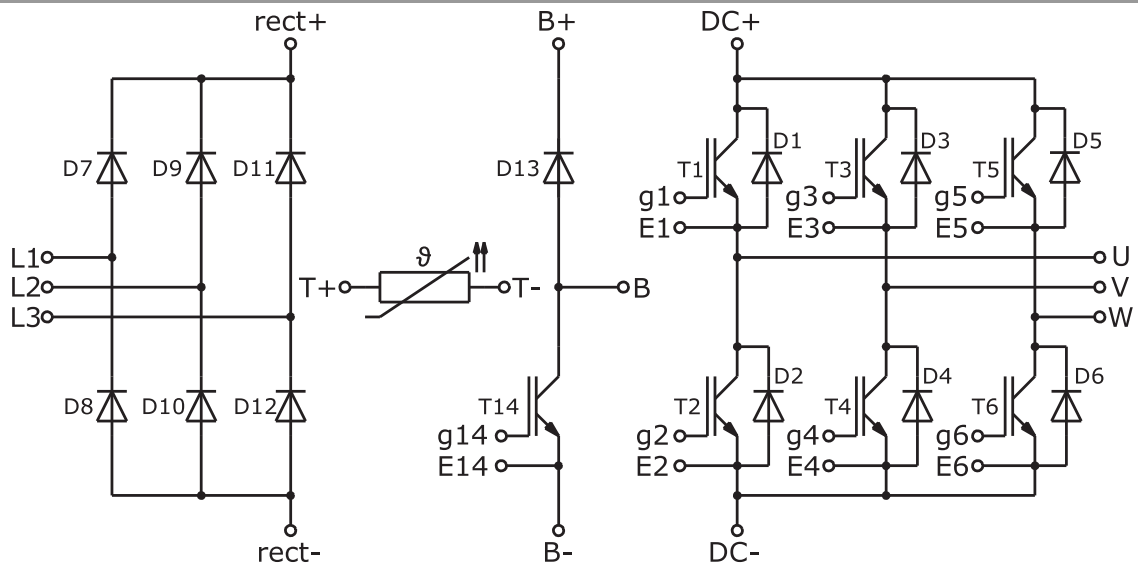


Fig. 12: Typ. input bridge forward characteristic

all values in mm





Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

*IMPORTANT INFORMATION AND WARNINGS

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